16-Channel Wideband Video Multiplexers

FEATURES

- Crosstalk: –100 dB @ 5 MHz
- 300 MHz Bandwidth
- Low Input and Output Capacitance
- Low Power: 75 µW
- Low $r_{DS(on)}$: 50 Ω
- On-Board Address Latches
- Disable Output

BENEFITS

- High Video Quality
- Reduced Insertion Loss
- Reduced Input Buffer Requirements
- Minimizes Power Consumption
- Simplifies Bus Interface

APPLICATIONS

- Video Switching/Routing
- High Speed Data Routing
- RF Signal Multiplexing
- Precision Data Acquisition
- Crosspoint Arrays
- FLIR Systems

DESCRIPTION

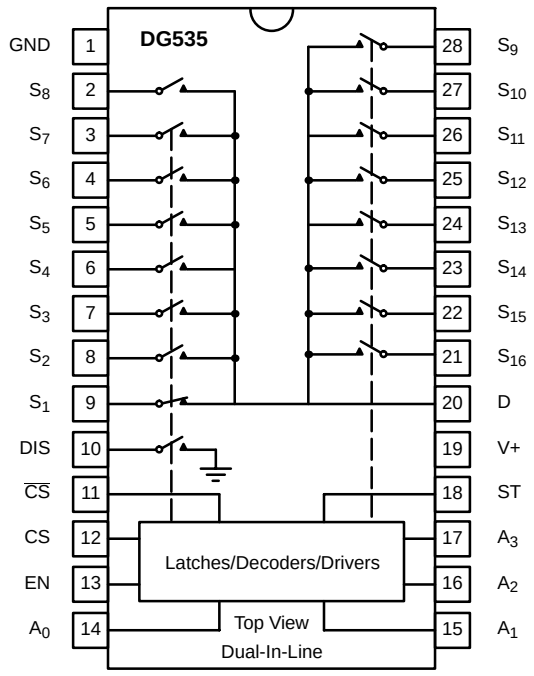
The DG535/536 are 16-channel multiplexers designed for routing one of 16 wideband analog or digital input signals to a single output. They feature low input and output capacitance, low on-resistance, and n-channel DMOS “T” switches, resulting in wide bandwidth, low crosstalk and high “off” isolation. In the on state, the switches pass signals in either direction, allowing them to be used as multiplexers or as demultiplexers.

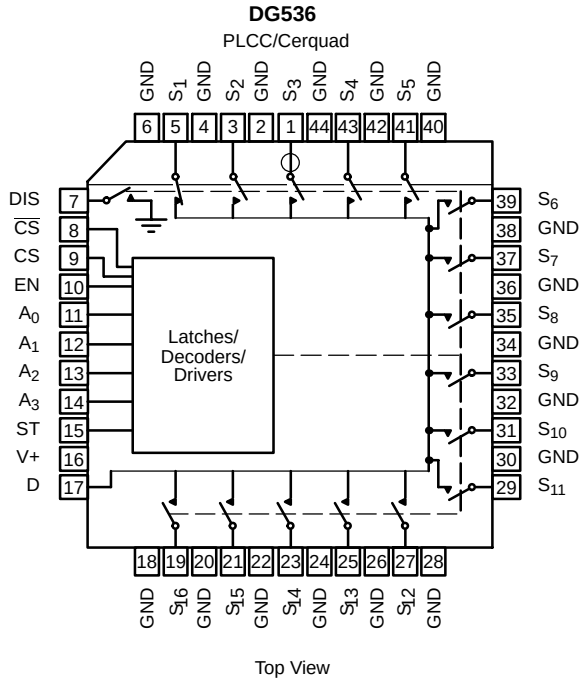
On-chip address latches and decode logic simplify microprocessor interface. Chip Select and Enable inputs simplify addressing in large matrices. Single-supply operation and a low 75-µW power consumption vastly reduces power supply requirements.

Theses devices are built on a proprietary D/CMOS process which creates low-capacitance DMOS FETs and high-speed, low-power CMOS logic on the same substrate.

For more information please refer to Vishay Siliconix Application Note AN501 (FaxBack document number 70608).

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





TRUTH TABLES AND ORDERING INFORMATION

ORDERING INFORMATION

Temperature Range	Package	Part Number
–40 to 85°C	28-Pin Plastic DIP	DG535DJ
	44-Pin PLCC	DG536DN
–55 to 125°C	28-Pin Sidebraze	DG535AP
		DG535AP/883
	44-Pin Cerquad	DG536AM/883

TRUTH TABLE

EN	CS	$\overline{CS}$	ST[a]	A_3	A_2	A_1	A_0	Channel Selected	Disable[b]
0	X	X	1	X	X	X	X	None	High Z
X	0	X							
X	X	1							
1	1	0	1	0	0	0	0	S_1	Low Z
				0	0	0	1	S_2	
				0	0	1	0	S_3	
				0	0	1	1	S_4	
				0	1	0	0	S_5	
				0	1	0	1	S_6	
				0	1	1	0	S_7	
				0	1	1	1	S_8	
				1	0	0	0	S_9	
				1	0	0	1	S_{10}	
				1	0	1	0	S_{11}	
				1	0	1	1	S_{12}	
				1	1	0	0	S_{13}	
				1	1	0	1	S_{14}	
				1	1	1	0	S_{15}	
				1	1	1	1	S_{16}	
X	X	X	0	X	X	X	X	Maintains previous switch condition	High Z or Low Z

Logic "0" = $V_{AL} \leq 4.5$ V
Logic "1" = $V_{AH} \geq 10.5$ V
X = Don't Care

Notes:
a. Strobe input (ST) is level triggered.
b. Low Z, High Z = impedance of Disable Output to GND. Disable output sinks current when any channel is selected.

ABSOLUTE MAXIMUM RATINGS

V+ to GND ..... –0.3 V to +18 V
Digital Inputs ..... (GND – 0.3 V) to (V+ plus 2 V) or 20 mA, whichever occurs first
V_S, V_D ..... (GND – 0.3 V) to V+ plus 2 V) or 20 mA, whichever occurs first
Current (any terminal) Continuous ..... 20 mA
Current (S or D) Pulsed 1 ms 10% duty cycle ..... 40 mA
Storage Temperature (A Suffix) ..... –65 to 150°C
(D Suffix) ..... –65 to 125°C
Power Dissipation (Package)[a]
28-Pin Plastic DIP[b] ..... 625 mW
28-Pin Sidebraze[c] ..... 1200 mW
44-Pin PLCC[d] ..... 450 mW
44-Pin Cerquad[e] ..... 825 mW

Notes:
a. All leads soldered or welded to PC board.
b. Derate 8.6 mW/°C above 75°C.
c. Derate 16 mW/°C above 75°C.
d. Derate 6 mW/°C above 75°C.
e. Derate 11 mW/°C above 75°C.

SPECIFICATIONS[a]

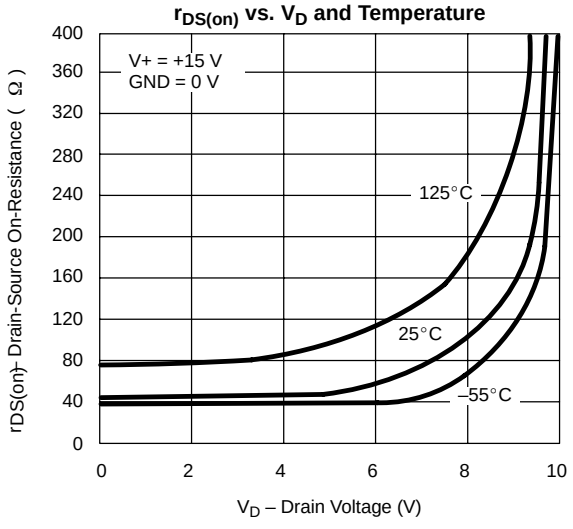
Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 15 V, ST, CS = 10.5 V $\overline{CS}$ = 4.5 V, V_A = 4.5 or 10.5 V[f]		Temp[b]	Typ[c]	A Suffix –55 to 125°C Min[c]	A Suffix –55 to 125°C Max[c]	D Suffix –40 to 85°C Min[c]	D Suffix –40 to 85°C Max[c]	Unit
Analog Switch										
Analog Signal Range[e]	V_{ANALOG}			Full		0	10	0	10	V
Drain-Source On-Resistance	$r_{DS(on)}$	I_S = –1 mA, V_D = 3 V EN = 10.5 V Sequence Each Switch On		Room Full	55		90 120		90 120	Ω
Resistance Match	$\Delta r_{DS(on)}$			Room			9		9	
Source Off Leakage Current	$I_{S(off)}$	V_S = 3 V, V_D = 0 V, EN = 4.5 V		Room Full		–10 –100	10 100	–10 –100	10 100	nA
Drain On Leakage Current	$I_{D(on)}$	V_S = V_D = 3 V, EN = 10.5 V		Room Full		–10 –1000	10 1000	–10 –100	–10 –100	
Disable Output	$R_{DISABLE}$	$I_{DISABLE}$ = 1 mA, EN = 10.5 V		Room Full	100		200 250		200 250	Ω
Digital Control										
Input Voltage High	V_{AIH}			Full		10.5		10.5		V
Input Voltage Low	V_{AIL}			Full			4.5		4.5	
Address Input Current	I_{AI}	V_A = GND or V+		Room Full	<0.01	–1 –100	1 100	–1 –100	1 100	µA
Address Input Capacitance	C_A			Full	5					pF
Dynamic Characteristics										
On State Input Capacitance[e]	$C_{S(on)}$	V_D = V_S = 3 V	PLCC	Room	32		45		45	pF
			Cerquad	Room	35					
			DIP	Room	40		55		55	
Off State Input Capacitance[e]	$C_{S(off)}$	V_S = 3 V	PLCC	Room	2		8		8	
			Cerquad	Room	5					
			DIP	Room	3					
Off State Output Capacitance[e]	$C_{D(off)}$	V_D = 3 V	PLCC	Room	8		20		20	
			Cerquad	Room	12					
			DIP	Room	9					
Multiplexer Switching Time	t_{TRANS}	See Figure 4		Full			300		300	ns
Break-Before-Make Interval	t_{OPEN}			Full		25		25		
EN, CS, $\overline{CS}$, ST, t_{ON}	t_{ON}	See Figure 2 and 3		Full			300		300	
EN, CS, $\overline{CS}$, ST, t_{OFF}	t_{OFF}	See Figure 2		Full			150		150	
Charge Injection	Q	See Figure 5		Room	–35					pC
Single-Channel Crosstalk	$X_{TALK(SC)}$	R_{IN} = 75 Ω R_L = 75 Ω f = 5 MHz See Figure 9	PLCC	Room	–100					dB
			Cerquad	Room	–93					
			DIP	Room	–60					
Chip Disabled Crosstalk	$X_{TALK(CD)}$	R_{IN} = R_L = 75 Ω f = 5 MHz EN = 4.5 V See Figure 8	PLCC	Room	–85					
			Cerquad	Room	–84					
			DIP	Room	–60					

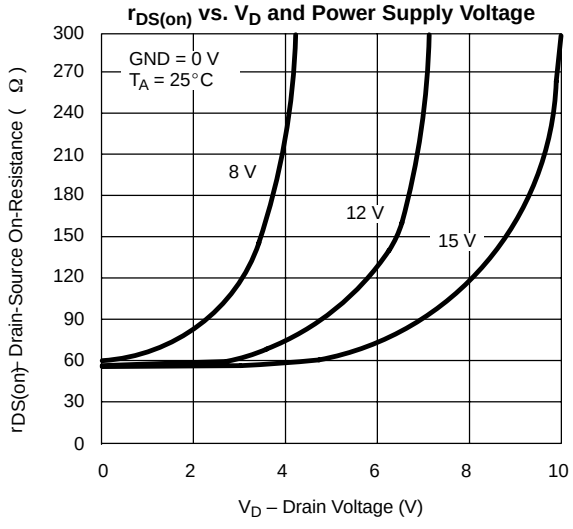
SPECIFICATIONS[a]

Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 15 V, ST, CS = 10.5 V $\overline{CS}$ = 4.5 V, V_A = 4.5 or 10.5 V[f]		Temp[b]	Typ[c]	A Suffix –55 to 125°C Min[c]	A Suffix –55 to 125°C Max[c]	D Suffix –40 to 85°C Min[c]	D Suffix –40 to 85°C Max[c]	Unit
Dynamic Characteristics (Cont'd)										
Adjacent Input Crosstalk	$X_{TALK(AI)}$	R_{IN} = 10 Ω, R_L = 10 kΩ, f = 5 MHz, See Figure 10	PLCC	Room	–92					dB
			Cerquad	Room	–87					
			DIP	Room	–72					
All Hostile Crosstalk[e]	$X_{TALK(AH)}$	R_{IN} = 10 Ω, R_L = 10 kΩ, f = 5 MHz, See Figure 7	PLCC	Room	–74	–60		–60		
			Cerquad	Room	–74					
			DIP	Room	–60					
Bandwidth	BW	R_L = 50 Ω, See Figure 6		Room	500					MHz
Power Supplies										
Positive Supply Current	I+	Any One Channgel Selected with All Logic Inputs at GND or V+		Room Full	5		50 100		50 100	µA
Supply Voltage Range	V+			Full		10	16.5	10	16.5	V
Minimum Input Timing Requirements										
Strobe Pulse Width	t_{SW}	See Figure 1		Full		200		200		ns
A_0, A_1, A_2, A_3 CS, $\overline{CS}$, EN Data Valid to Strobe	t_{DW}			Full		100		100		
A_0, A_1, A_2, A_3 CS, $\overline{CS}$, EN Data Valid after Strobe	t_{WD}			Full		50		50		

Notes:
a. Refer to PROCESS OPTION FLOWCHART.
b. Room = 25°C, Full = as determined by the operating temperature suffix.
c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
e. Guaranteed by design, not subject to production test.
f. V_A = input voltage to perform proper function.

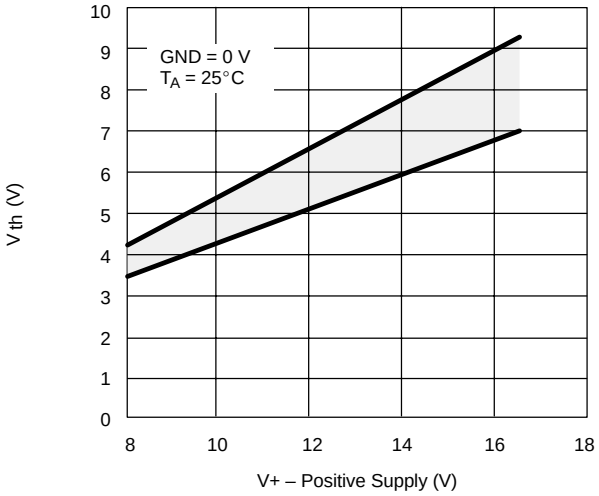
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



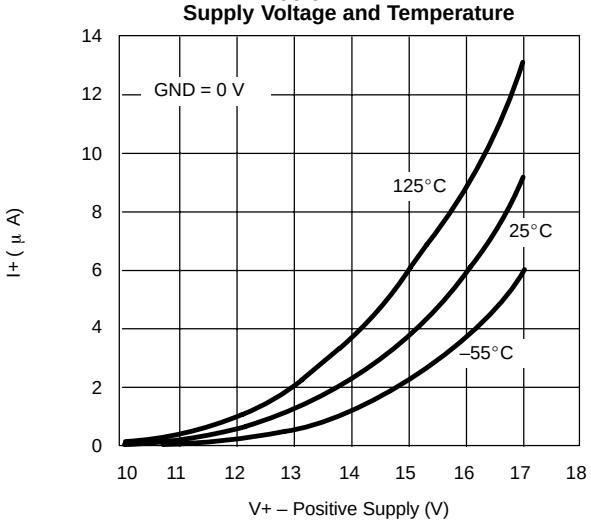


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

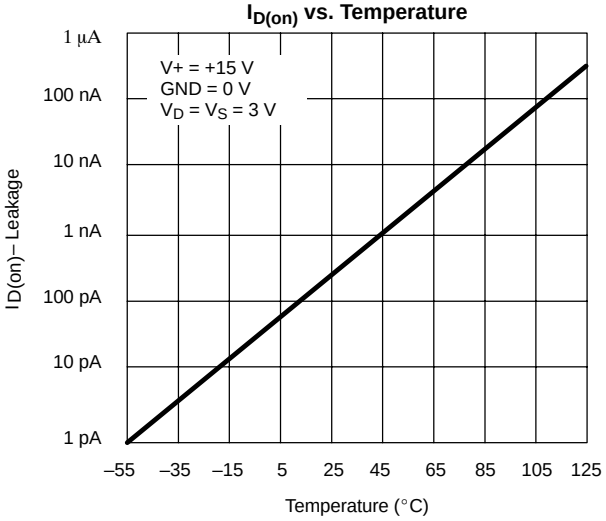
Logic Input Switching Threshold vs. Supply Voltage (V+)



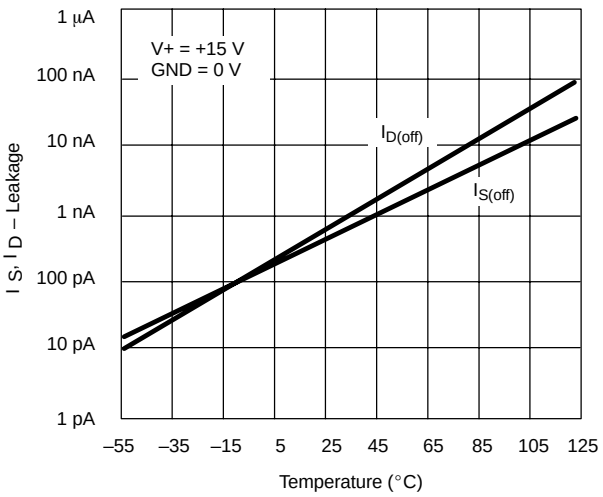
Supply Current vs. Supply Voltage and Temperature



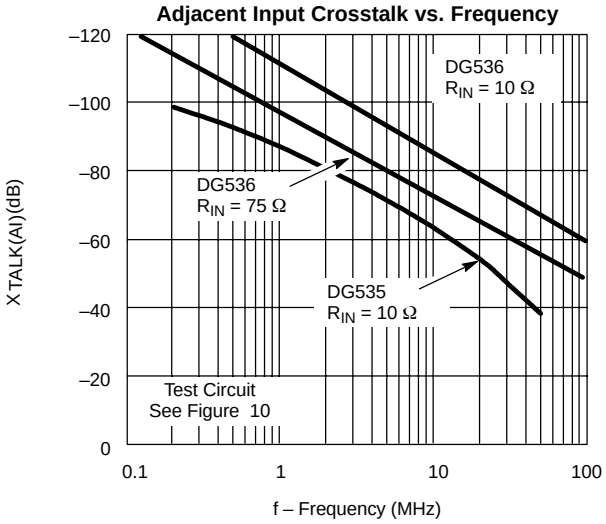
$I_{D(on)}$ vs. Temperature



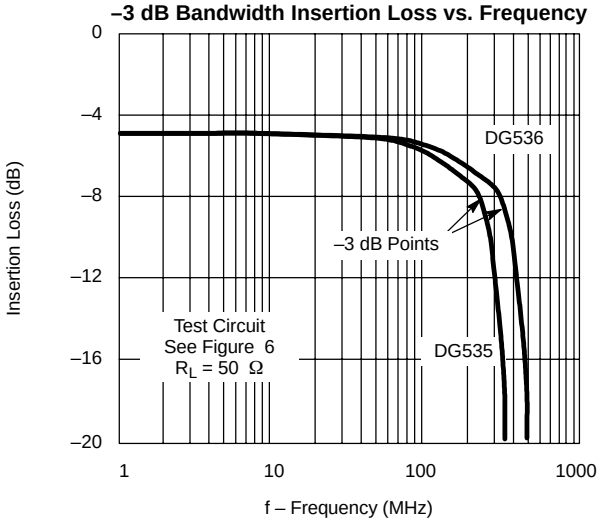
Leakage Current vs. Temperature



Adjacent Input Crosstalk vs. Frequency

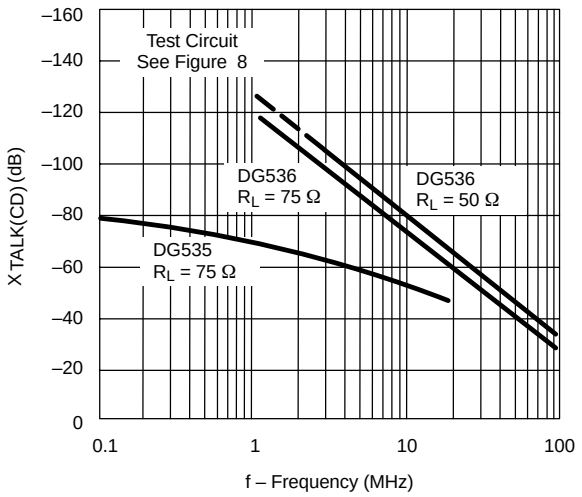


–3 dB Bandwidth Insertion Loss vs. Frequency

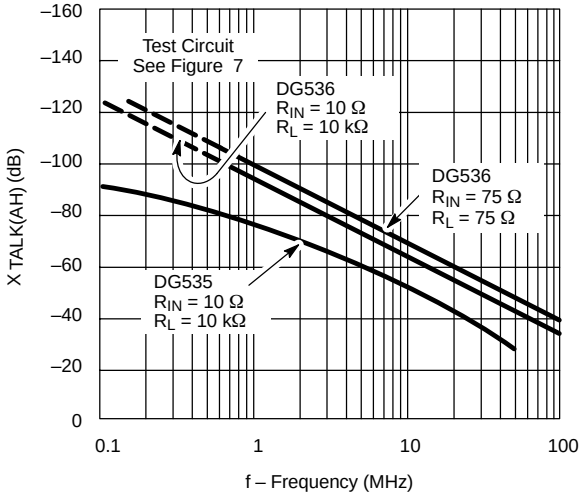


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

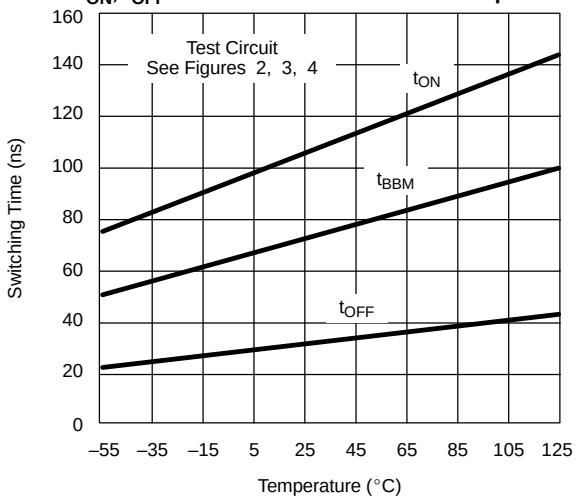
Chip Disable Crosstalk vs. Frequency



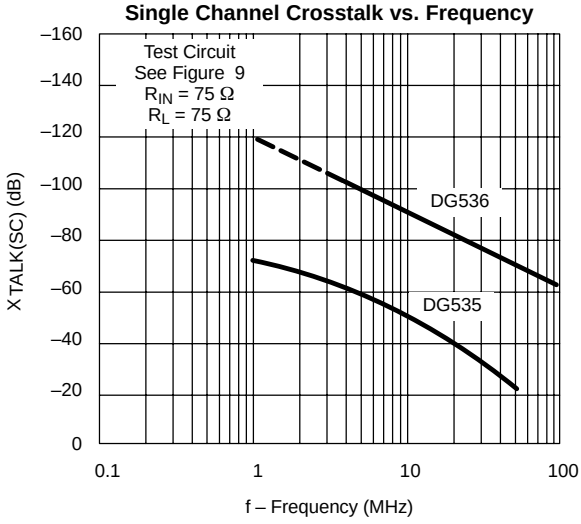
All Hostile Crosstalk vs. Frequency



t_{ON}, t_{OFF} and Break-Before-Make vs. Temperature



Single Channel Crosstalk vs. Frequency



INPUT TIMING REQUIREMENTS

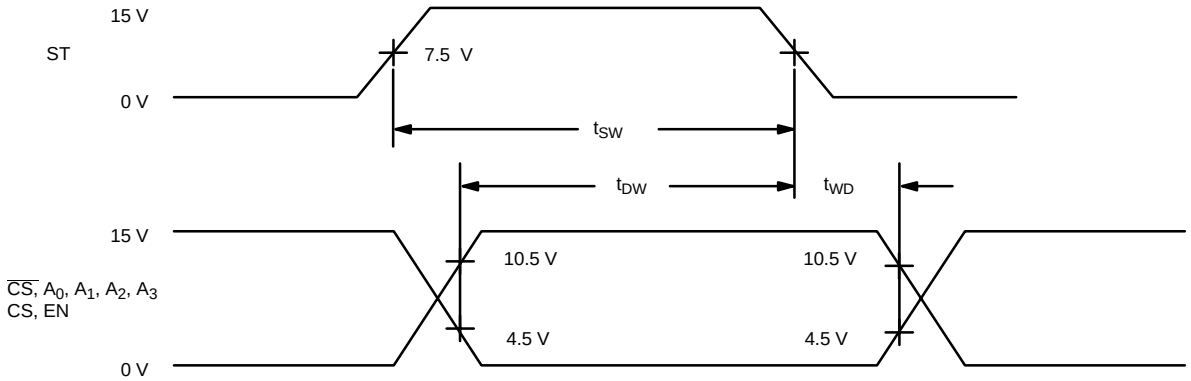


FIGURE 1.

TEST CIRCUITS

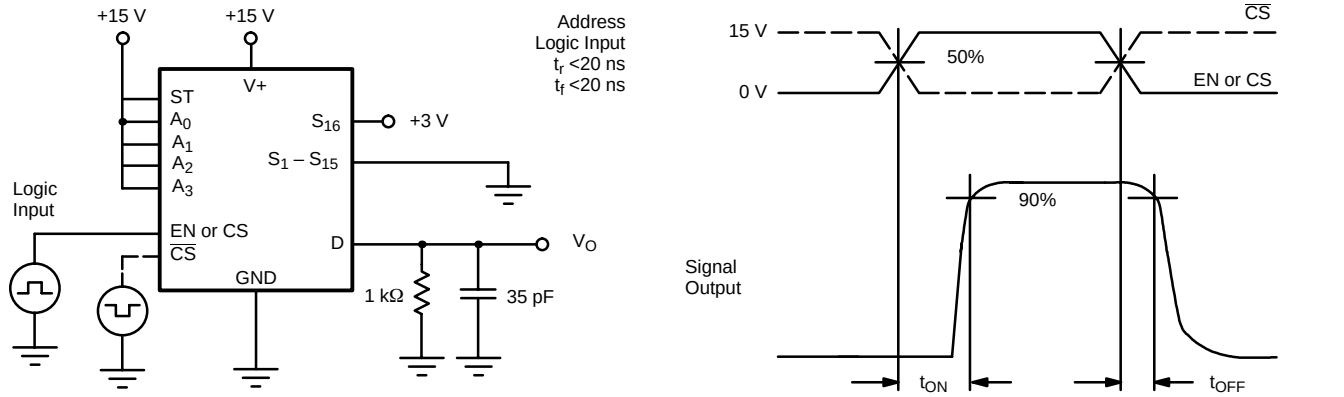


FIGURE 2. EN, CS, $\overline{CS}$, Turn On/Off Time

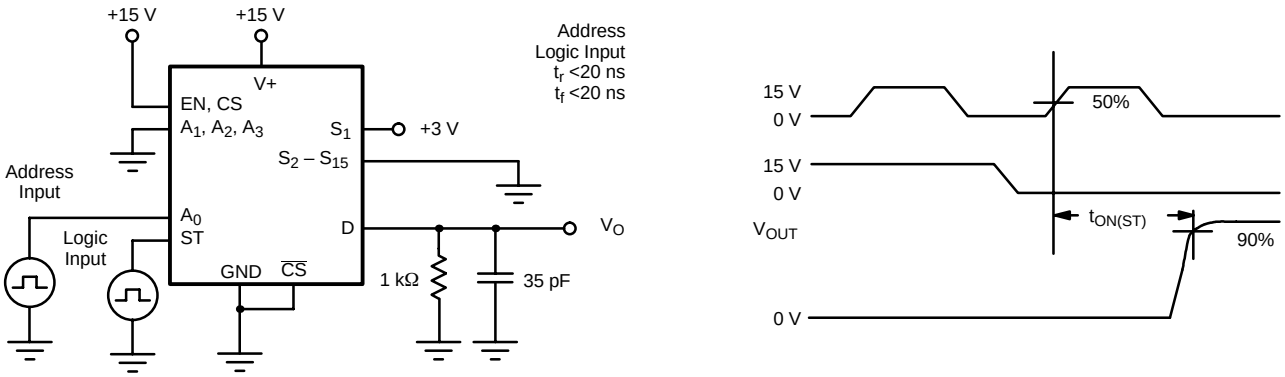


FIGURE 3. Strobe ST Turn On Time

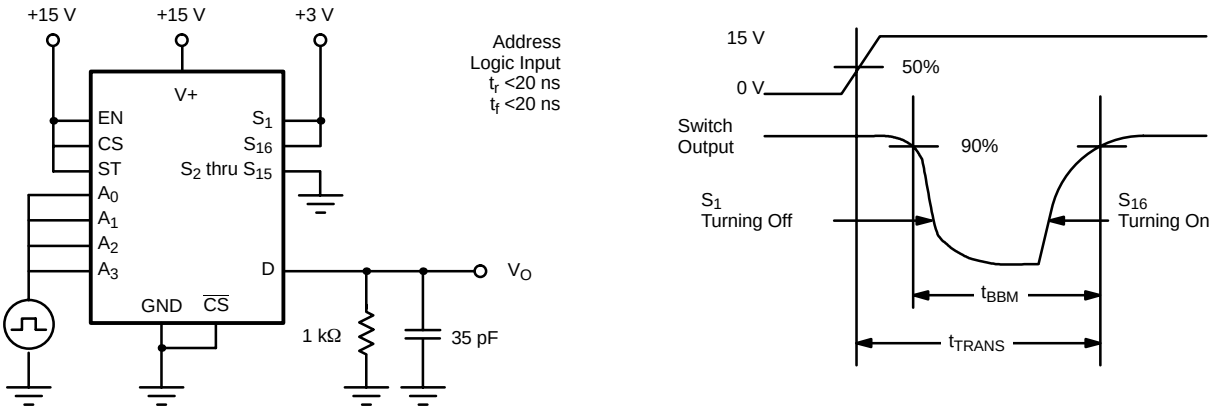
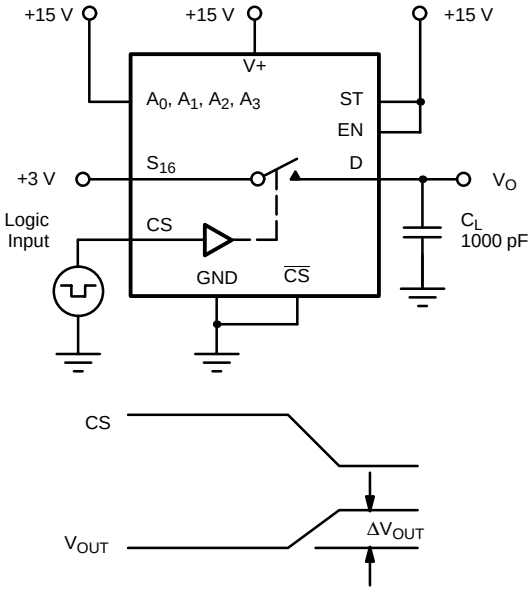


FIGURE 4. Transition Time and Break-Before-Make Interval

TEST CIRCUITS



ΔV_{OUT} is the measured voltage error due to charge injection.
The charge injection in Coulombs is $Q = C_L \times \Delta V_{OUT}$

FIGURE 5. Charge Injection

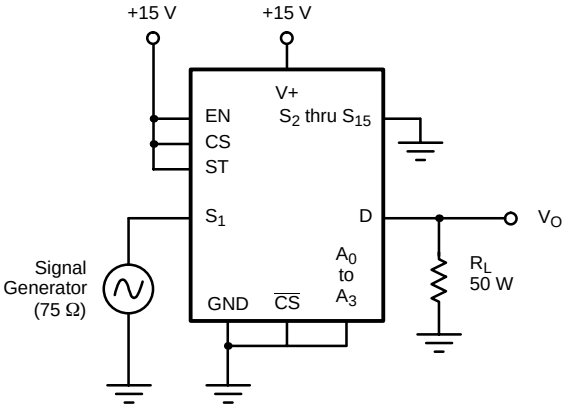


FIGURE 6. Bandwidth

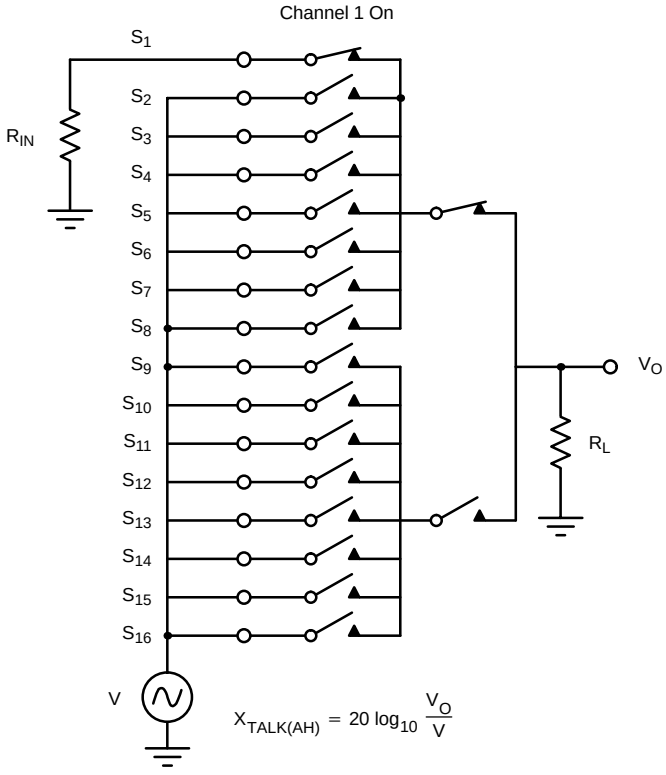


FIGURE 7. All Hostile Crosstalk

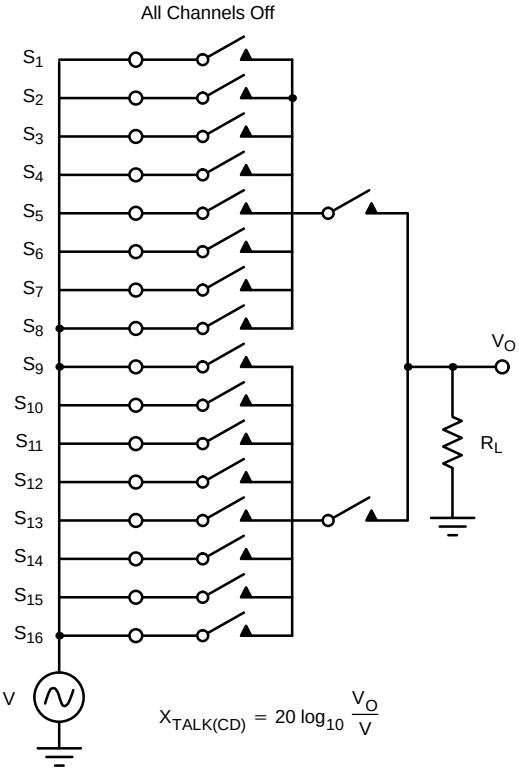
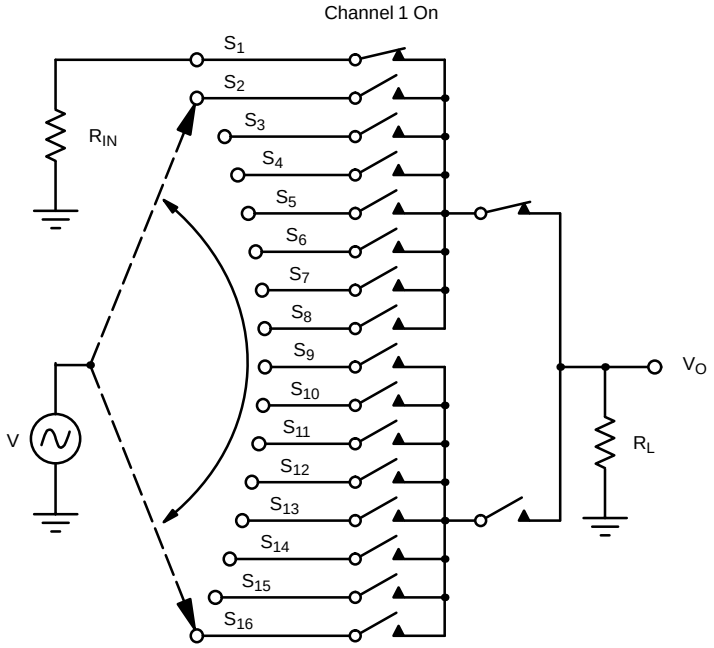


FIGURE 8. Chip Disabled Crosstalk

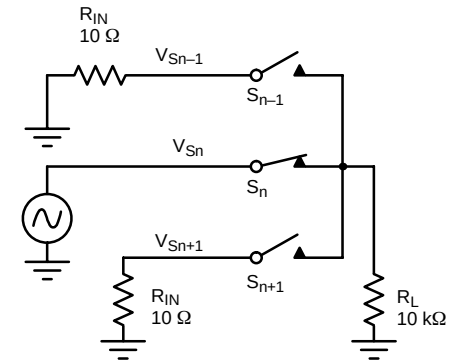
TEST CIRCUITS



Notes:

1. Any individual channel between S_2 and S_{16} can be selected
2. $X_{TALK(SC)} = 20 \log_{10} \frac{V_O}{V}$ is scanned sequentially from S_2 to S_{16}

FIGURE 9. Single Channel Crosstalk



$$X_{TALK(AI)} = 20 \log_{10} \frac{V_{Sn-1}}{V_{Sn}} \text{ or } 20 \log_{10} \frac{V_{Sn+1}}{V_{Sn}}$$

FIGURE 10. Adjacent Input Crosstalk

PIN DESCRIPTION	
Symbol	**Description**
S_1 thru S_{16}	Analog inputs/outputs
D	Multiplexer output/demultiplexer input
DIS	Open drain low impedance to analog ground when any channel is selected
$\overline{CS}$, CS, EN	Logic inputs to selected desired multiplexer(s) when using several multiplexers in a system
A_0 thru A_3	Binary address inputs to determine which channel is selected
ST	Strobe input that latches A_0, A_1, A_2, A_3, $\overline{CS}$, CS, EN
V+	Positive supply voltage input
GND	Analog signal ground and most negative potential **All ground pins should be connected externally to ensure dynamic performance**

DETAILED DESCRIPTION

The DG535/536 are 16-channel single-ended multiplexers with on-chip address logic and control latches.

The multiplexer connects one of sixteen inputs (S_1, S_2 through S_{16}) to a common output (D) under the control of a 4-bit binary address (A_0 to A_3). The specific input channel selected for each address is given in the Truth Table.

All four address inputs have on-chip data latches which are controlled by the Strobe (ST) input. These latches are transparent when Strobe is high but they maintain the chosen address when Strobe goes low. To facilitate easy microprocessor control in large matrices a choice of three independent logic inputs (EN, CS and $\overline{CS}$) are provided on chip. These inputs are gated together (see Figure 11) and only when EN = CS = 1 and $\overline{CS}$ = 0 can an output switch be selected. This necessary logic condition is then latched-in when Strobe (ST) goes low.

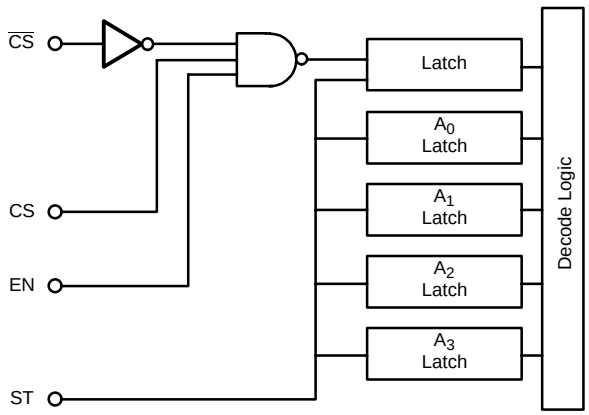


FIGURE 11. $\overline{CS}$, CS, EN, ST Control Logic

Break-before-make switching prevents momentary shorting when changing from one input to another.

The devices feature a two-level switch arrangement whereby two banks of eight switches (first level) are connected via two series switches (second level) to a common DRAIN output.

In order to improve crosstalk all sixteen first level switches are configured as “T” switches (see Figure 12).

With this method SW_2 operates out of phase with SW_1 and SW_3. In the on condition SW_1 and SW_3 are closed with SW_2 open whereas in the off condition SW_1 and SW_3 are open and SW_2 closed. In the off condition the input to SW_3 is effectively the isolation leakage of SW_1 working into the on-resistance of SW_2 (typically 200 Ω).

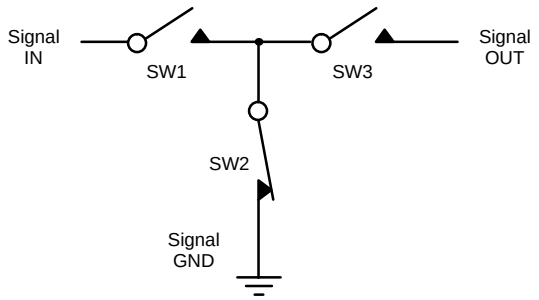


FIGURE 12. “T” Switch Arrangement

The two second level series switches further improve crosstalk and help to minimize output capacitance.

The DIS output can be used to signal external circuitry. DIS is a high impedance to GND when no channel is selected and a low impedance to GND when any one channel is selected.

The DG535/536 have extensive applications where any high frequency video or digital signals are switched or routed. Exceptional crosstalk and bandwidth performance is achieved by using n-channel DMOS FETs for the “T” and series switches.

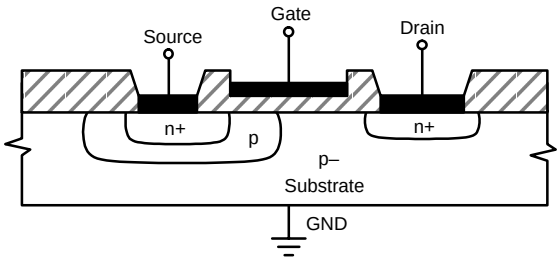


FIGURE 13. Cross-Section of a Single DMOS Switch

It can clearly be seen from Figure 13 that there exists a PN junction between the substrate and the drain/source terminals.

Should a signal which is negative with respect to the substrate (GND pin) be connected to a source or drain terminal, then the PN junction will become forward biased and current will flow between the signal source and GND. This effective shorting of the signal source to GND will not necessarily cause any damage to the device, provided that the total current flowing is less than the maximum rating, (i.e., 20 mA).

DETAILED DESCRIPTION

Since no PN junctions exist between the signal path and V+, positive overvoltages are not a problem, unless the breakdown voltage of the DMOS drain terminal (see Figure 13) (+18 V) is exceeded. Positive overvoltage conditions must not exceed +18 V with respect to the GND pin. If this condition is possible (e.g. transients in the signal), then a diode or Zener clamp may be used to prevent breakdown.

The overvoltage conditions described may exist if the supplies are collapsed while a signal is present on the inputs. If this condition is unavoidable, then the necessary steps outlined above should be taken to protect the device

DC Biasing

To avoid negative overvoltage conditions and subsequent distortion of ac analog signals, dc biasing may be necessary. Biasing is not required, however, in applications where signals are always positive with respect to the GND or substrate connection, or in applications involving multiplexing of low level (up to ±200 mV) signals, where forward biasing of the PN substrate-source/drain terminals would not occur.

Biasing can be accomplished in a number of ways, the simplest of which is a resistive potential divider and a few dc blocking capacitors as shown in Figure 14.

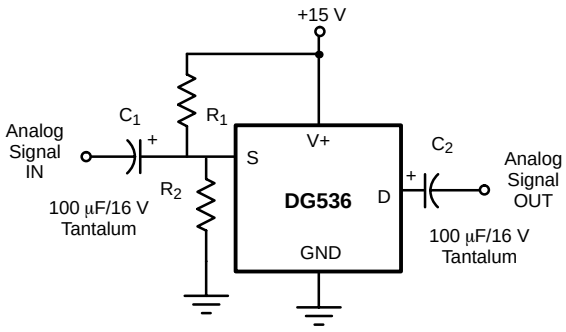


FIGURE 14. Simple Bias Circuit

R_1 and R_2 are chosen to suit the appropriate biasing requirements. For video applications, approximately 3 V of bias is required for optimal differential gain and phase performance. Capacitor C_1 blocks the dc bias voltage from being coupled back to the analog signal source and C_2 blocks the dc bias from the output signal. Both C_1 and C_2 should be tantalum or ceramic disc type capacitors in order to operate efficiently at high frequencies. Active bias circuits are recommended if rapid switching time between channels is required.

An alternative method is to offset the supply voltages (see Figure 15).

Decoupling would have to be applied to the negative supply to ensure that the substrate is well referenced to signal ground. Again the capacitors should be of a type offering good high frequency characteristics.

Level shifting of the logic signals may be necessary using this offset supply arrangement.

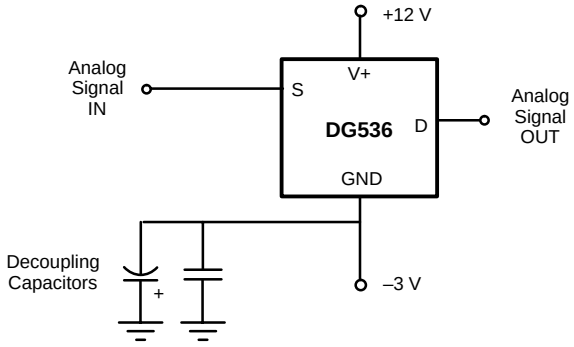


FIGURE 15. DG536 with Offset Supply

TTL to CMOS level shifting is easily obtained by using a MC14504B.

Circuit Layout

Good circuit board layout and extensive shielding is essential for optimizing the high frequency performance of the DG536. Stray capacitances on the PC board and/or connecting leads will considerably degrade the ac performance. Hence, signal paths must be kept as short as practically possible, with extensive ground planes separating signal tracks.